

A Soluble Salts-Assisted Facile Synthetic Route to Semiconducting GaN Nanoparticles

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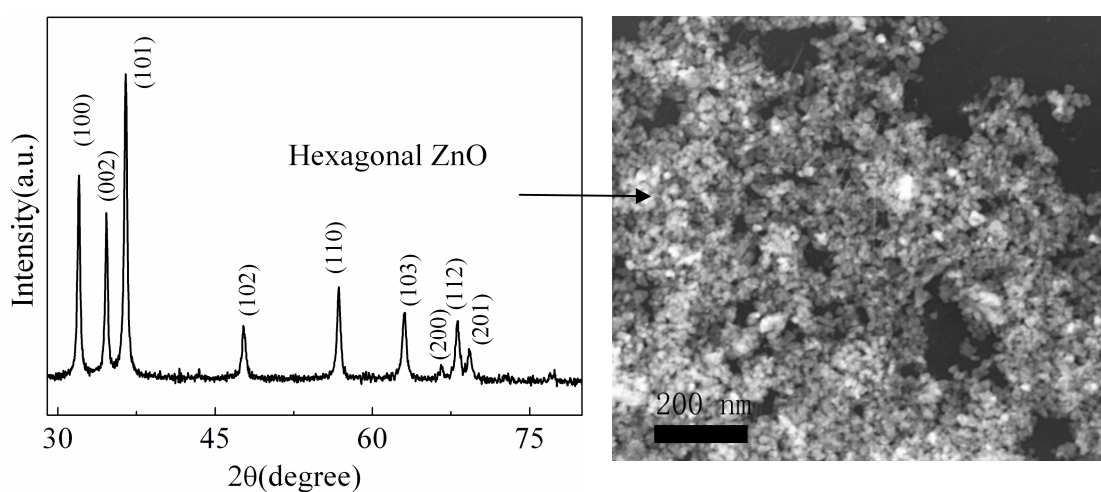
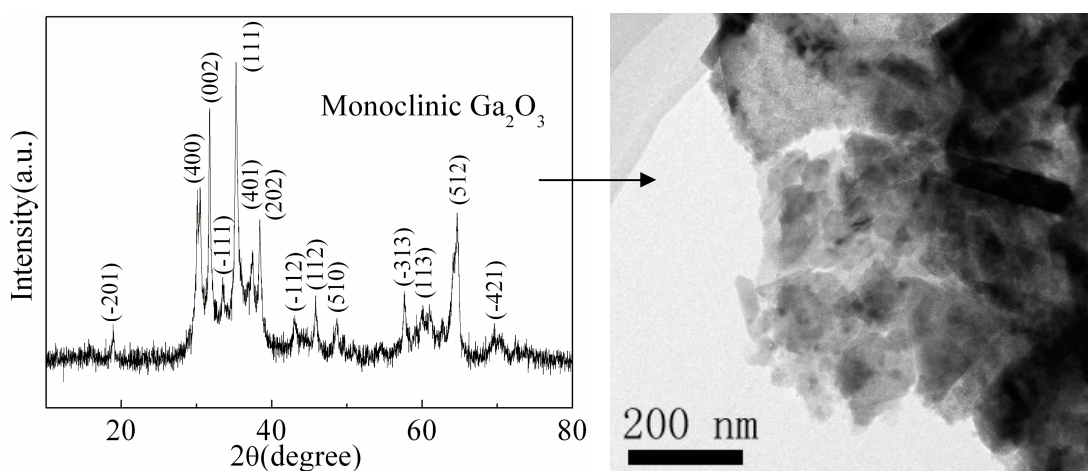
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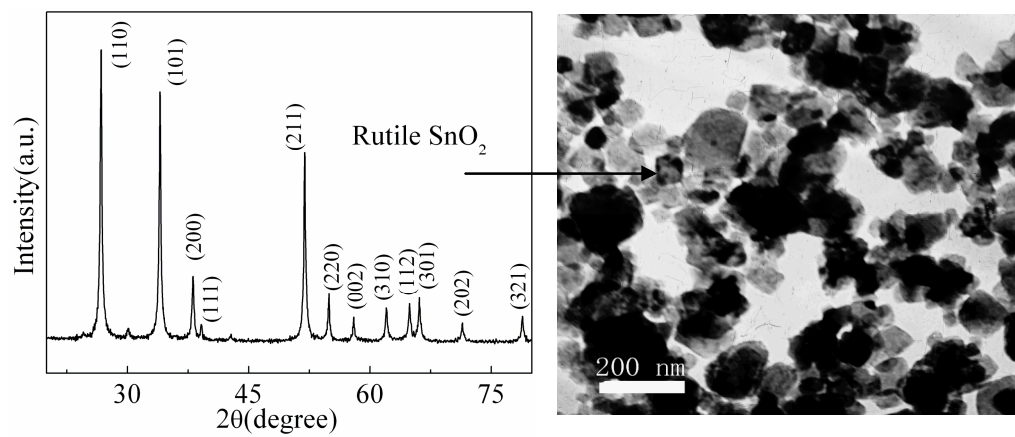
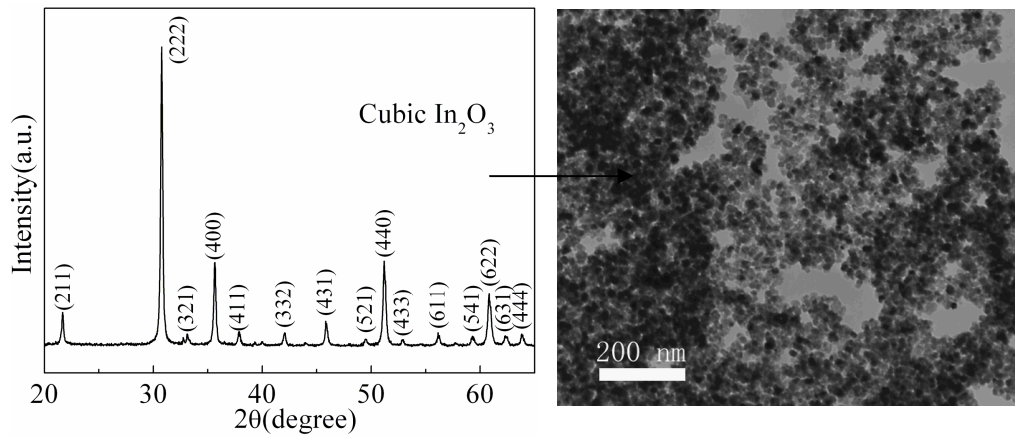
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Index 1: XRD patterns and TEM images of Ga₂O₃, ZnO, In₂O₃ and SnO₂ NPs.





Note: The preparation process of Ga_2O_3 NPs is similar to that of the GaN NPs just except the replacement of NH_3 with air. Some other oxides nanostructures are prepared by ball-milling metal powder- Na_2SO_4 mixtures followed with the oxidation in air and washing with distilled water.